

ABSTRACT

The present invention is intended to provide a cerium-oxide chemical mechanical polishing solution. Adding a quaternary ammonium compound to a cerium-oxide polishing solution can increase the polishing rate of SiN to 1.5 times or more, and the polishing rate of TEOS is virtually unaffected. By taking tetrabutylammonium hydroxide and benzyltriethylammonium chloride as an example, the content of which is 200-1,000 ppm, a pH of the polishing solution in the range of 4.0-6.0 can improve the polishing rate of the polishing solution for SiN.

(No suitable figure)